PATENT COOPERATION TREATY REC'D 21 JUL 2004

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## INTERNATIONAL PRELIMINARY EXAMINATION REPORT

(PCT Article 36 and Rule 70)

Applicant's or agent's file reference	FOR FURTHER ACTION	See Notification Preliminary E	on of Transmittal of International xamination Report (Form PCT/IPEA/416)	
International application No.	International filing date (day/mor	th/year)	Priority date (day/month/year)	
PCT/US03/03323	03 February 2003 (03.02.2003)		01 February 2002 (01.02.2002)	
International Patent Classification (IPC)	or national classification and IPC		01 1 torum y 2002 (01.02.2002)	
IPC(7): H01L 31/072, 31/109, 31/0328	and US Cl.: 257/183, 183, 185, 18	36, 190, 191		
Applicant				
PICOMETRIX, INC.				
1. This international preliminary examination report has been prepared by this International Preliminary Examining Authority and is transmitted to the applicant according to Article 36.				
2. This REPORT consists of	2. This REPORT consists of a total of \(\frac{1}{2}\) sheets, including this cover sheet.			
This report is also accompanied by ANNEXES, i.e., sheets of the description, claims and/or drawings which have been amended and are the basis for this report and/or sheets containing rectifications made before this Authority (see Rule 70.16 and Section 607 of the Administrative Instructions under the PCT).				
These annexes consist of a	total of sheets.			
3. This report contains indica	tions relating to the following i	tems:		
I Basis of the repo	I Basis of the report			
II Priority				
III Non-establishment of report with regard to novelty, inventive step and industrial applicability				
IV Lack of unity of invention				
V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement				
l —				
VII 🔀 Certain defects in				
VIII Certain observati	ions on the international applica	ation		
Date of submission of the demand	Date o	of completion of	of this report	
	18 Ma	rch 2004 (18.03	.2004)	
Name and mailing address of the IPEA/US  Mail Stop PCT, Atm: IPEA/US		ized officer	2	
Commissioner for Patents P.O. Box 1450	Minh-	Loan T. Tran	eggyttamod	
Alexandria, Virginia 22313-1450		one No. (571) 2	272-1922	
Facsimile No. (703) 305-3230 Telephone No. (5/1) 272-1922				

Form PCT/IPEA/409 (cover sheet)(July 1998)



International application	
PCT/US03/03323	

I.	Basis	s of the report
		regard to the elements of the international application:*
	$\boxtimes$	the international application as originally filed.
	X	the description:
	E_3	pages 1-9 as originally filed
		pages NONE , filed with the demand
		pages NONE , filed with the letter of
	$\boxtimes$	the claims:
		pages 10-13 , as originally filed
		pages NONE , as amended (together with any statement) under Article 19
		pages NONE , filed with the demand pages NONE , filed with the letter of
	$\square$	
ì		the drawings: pages 1-2 , as originally filed
		pages NONE , filed with the demand
		pages NONE , filed with the letter of
	П	the sequence listing part of the description:
		pages NONE , as originally filed
1		pages NONE , filed with the demand
		pages NONE filed with the letter of
2	. Wit	th regard to the language, all the elements marked above were available or furnished to this Authority in the
	lang The	guage in which the international application was filed, unless otherwise indicated under this item. see elements were available or furnished to this Authority in the following language which is:
		the language of a translation furnished for the purposes of international search (under Rule23.1(b)).
		the language of publication of the international application (under Rule 48.3(b)).
		the language of the translation furnished for the purposes of international preliminary examination(under Rules
	-	55.2 and/or 55.3).
:	3. Wi inte	th regard to any nucleotide and/or amino acid sequence disclosed in the international application, the ernational preliminary examination was carried out on the basis of the sequence listing:
		contained in the international application in printed form.
		filed together with the international application in computer readable form.
		furnished subsequently to this Authority in written form.
		furnished subsequently to this Authority in computer readable form.
		The statement that the subsequently furnished written sequence listing does not go beyond the disclosure in the international application as filed has been furnished.
		The statement that the information recorded in computer readable form is identical to the written sequence listing has been furnished.
1	4. 🗵	The amendments have resulted in the cancellation of:
		the description, pages None
		the claims, Nos. 17,18,22 and 24
		the drawings, sheets/fig None
	5.	This report has been established as if (some of) the amendments had not been made, since they have been considered to go beyond the disclosure as filed, as indicated in the Supplemental Box (Rule 70.2(c)).**
	this ra	lacement sheets which have been furnished to the receiving Office in response to an invitation under Article 14 are referred to in port as "originally filed" and are not annexed to this report since they do not contain amendments (Rules 70.16 and 70.17). To replacement sheet containing such amendments must be referred to under item 1 and annexed to this report.
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Form PCT/IPEA/409 (Box I) (July 1998)

V. Reasoned statement under Rule 66.2(a)(ii) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement			
1. STATEMENT			
Name In AD	Claims	1-8,10,11,13,14 and 17-25	YES
Novelty (N)		9,12,15 and 16	NO
Inventive Step (IS)	Claims	1-8,10,11 and 17-25	YES
	Claims	9, 12-16	ио
	<b>.</b> .		YES
Industrial Applicability (IA)	Claims		NO
	Cianni	NONE	
Yasuda et al. discloses a method of fabricating a platype semiconductor layer 2 defining a contact area is semiconductor layer 2; depositing a second n-type semiconductor multiplication layer 5; depositing an wherein the p-type diffusion region 8 is disposed di 8 having a smaller area than the n-type semiconduct photodiode. Note figure 3 of Yasuda et al.  Claims 13-15 lack an inventive step under PCT Art Yasuda et al. does not disclose the first and second the absorption layer is InGaAs. Although Yasuda et al. semiconductor layers, the multiplication layer and considered obvious design choices and are not pate appears that these changes produce no functional di 416, In re Woodruff, 919 F.2d 1575, 1578, 16 US  Claims 9, 12, 15, 16 lack novelty under PCT Artic Watanabe discloses a planar avalanche photodiode an n-type contact layer 38 being disposed adjacent 32; a semiconductor multiplication layer 33; a semi 36 is disposed directly adjacent to the p-type contact decreasing the capacitance of the planar avalanche recite the semiconductor absorption layer being dishaving the p-type diffusion region as recited in cla  Claims 13 and 14 lack an inventive step under PC Watanabe does not disclose the first and second n-exact the material of the first and second n-exact the material of the first and second n-type seconsidered obvious design choices and are not pate appears that these changes produce no functional of the first and second n-type seconsidered obvious design choices and are not pate appears that these changes produce no functional of the first and second n-type seconsidered obvious design choices and are not pate appears that these changes produce no functional of the first and second n-type seconsidered obvious design choices and are not pate appears that these changes produce no functional of the first and second n-type seconsidered obvious design choices and are not pate appears that these changes produce no functional of the first and second n-type second n-type second n-type second n-type second n-type	ticle 33(3) as n-type semice tal. device de the absorption mable unless ifferences and PQ2d 1934, 1 cle 33(2) as becomprising a to the first n-ticonductor abect layer 37 an photodiode. It sposed between the tall of tal	being obvious over Yasuda et al. (4,840,916 onductor layers are InAlAs; the multiplication layer as that claimed by Applicant, the mate therefore would have been obvious. Note Instrumental of the first and layer as that claimed by Applicant, the mate therefore would have been obvious. Note Instrumental of the first and therefore would have been obvious. Note Instrumental of the first and therefore would have been obvious. Note Instrumental of the first and therefore would have been obvious. Note Instrumental of the first and the semiconductor layer 31 defining type semiconductor layer 31; a second netype sorption layer 35; a petype contact layer 37; defining a smaller area than the semiconductor figure 1 of Watanabe. Note that Applicant the semiconductor multiplication layer and 7-25.  By as being obvious over Watanabe (5,552,626) as being obvious over Watanabe (5,552,626) as being obvious over Watanabe (5,552,626) as that claimed by Applicant, the mate a unobvious or unexpected results are obtained therefore would have been obvious. Note Instrumental of therefore would have been obvious.	ype contact layer 17 p-type diffusion region nar avalanche  1).  In layer is InAlAs and nd second n-type erial differences are diffom these changes. It n re Leshin, 125 USPQ  a contact area wherein e semiconductor layer a p-type diffusion region stor layer 32, thereby ant's claim 9 does not di the semiconductor layer 29).  be device does not teach erial differences are act from these changes. It
Claims 1-8, 10, 11, 17-25 meet the criteria set our least one grading layer disposed adjacent to the n-charge control layer disposed adjacent to the n-typ absorption layer being disposed between the semi diffusion region as recited in claims 1-8 and 17-25	type semiconductor mu	eter multiplication layer as recited in claim 1	1 and the semiconductor
NEW CITATIONS			

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· INTERNATIONAL	PRELIMINARY E INATION REPORT

International application
PCT/US03/03323

VII. Certain defects in the international application	
The following defects in the form or contents of the international application have been noted:	•
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